

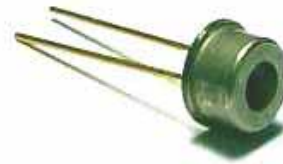
UV-B Sensor

GUVB-T11GD



Features

- Aluminium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- Good Visible Blindness
- High Responsivity & Low Dark Current



Applications

- Pure UV-B Monitoring
- UV Index Monitoring
- Sterilization Lamp Monitoring

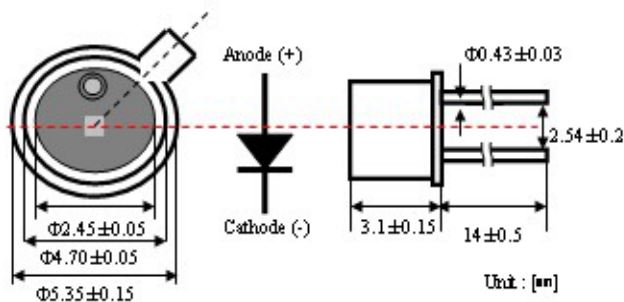
Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90	°C	
Operating Temperature	T_{op}	-30	85	°C	
Reverse Voltage	$V_{r, max.}$		3	V	
Forward Current	$I_{f, max.}$		1	mA	
Soldering Temperature	T_{sol}		260	°C	within 10 sec.

Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			1	nA	$V_r = 0.1$ V
Photo Current	I_{ph}		51		nA	UVB Lamp, $1\text{mW}/\text{cm}^2$
Temperature Coefficient	I_{tc}		0.05		%/°C	UVB Lamp
Responsivity	R		0.13		A/W	$\lambda = 300$ nm, $V_r = 0$ V
Spectral Detection Range	λ	220		320	nm	
Breakdown Voltage	V_{BR}		5			$I_r = 1$ μA

Outline Diagrams and Dimensions



Responsivity Curve

